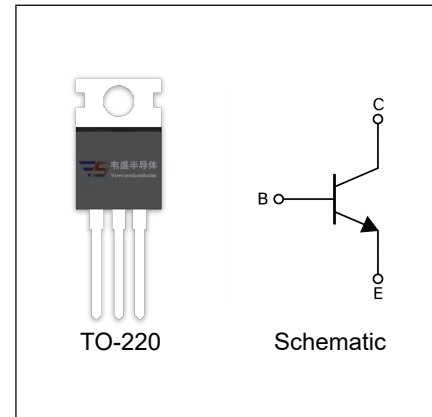


2SC4544 TRANSISTOR (NPN)

FEATURES

- High voltage: $V_{(BR)CEO} = 300\text{ V}$
- Small collector output capacitance: $C_{ob} = 3.0\text{ pF (typ.)}$
- Collector metal (fin) is fully covered with mold resin.



MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	300	V
V_{CEO}	Collector-Emitter Voltage	300	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current -Continuous	0.1	A
P_C	Collector Power Dissipation	2	W
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55-150	$^{\circ}\text{C}$

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	300			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10mA, I_B=0$	300			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	7			V
Collector cut-off current	I_{CBO}	$V_{CB}=240V, I_E=0$			1.0	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=7V, I_C=0$			1.0	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=10V, I_C=4mA$	20			
	$h_{FE(2)}$	$V_{CE}=10V, I_C=20mA$	30		200	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=10mA, I_B=1mA$			1.0	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=10mA, I_B=1mA$			1.0	V
Transition frequency	f_T	$V_{CE}=10V, I_C=20mA$	50	70		MHz
Collector output capacitance	C_{ob}	$V_{CB}=20V, I_E=0, f=1MHz$		3.0		pF

